Preferred Device

Sensitive Gate Silicon Controlled Rectifiers

Reverse Blocking Thyristors

PNPN devices designed for high volume, line-powered consumer applications such as relay and lamp drivers, small motor controls, gate drivers for larger thyristors, and sensing and detection circuits. Supplied in an inexpensive plastic TO-226AA package which is readily adaptable for use in automatic insertion equipment.

- Sensitive Gate Allows Triggering by Microcontrollers and Other Logic Circuits
- Blocking Voltage to 600 Volts
- On–State Current Rating of 0.8 Amperes RMS at 80°C
- High Surge Current Capability 10 Amperes
- Minimum and Maximum Values of IGT, VGT and IH Specified for Ease of Design
- Immunity to dV/dt 20 V/μsec Minimum at 110°C
- Glass-Passivated Surface for Reliability and Uniformity
- Device Marking: Device Type, e.g., MCR100-3, Date Code

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off–State Voltage ⁽¹⁾ (T _J = -40 to 110°C, Sine Wave, 50 to 60 Hz; Gate Open) MCR100-3 MCR100-4 MCR100-6 MCR100-8	VDRM, VRRM	100 200 400 600	Volts
On-State RMS Current (T _C = 80°C) 180° Conduction Angles	IT(RMS)	0.8	Amp
Peak Non-Repetitive Surge Current (1/2 Cycle, Sine Wave, 60 Hz, T _J = 25°C)	ITSM	10	Amps
Circuit Fusing Consideration (t = 8.3 ms)	l ² t	0.415	A ² s
Forward Peak Gate Power (T _A = 25°C, Pulse Width ≤ 1.0 μs)	PGM	0.1	Watt
Forward Average Gate Power (T _A = 25°C, t = 8.3 ms)	PG(AV)	0.10	Watt
Forward Peak Gate Current (Τ _A = 25°C, Pulse Width ≤ 1.0 μs)	IGM	1.0	Amp
Reverse Peak Gate Voltage $(T_A = 25^{\circ}C, \text{ Pulse Width } \leq 1.0 \mu\text{s})$	VGRM	5.0	Volts
Operating Junction Temperature Range @ Rate V _{RRM} and V _{DRM}	TJ	–40 to 110	°C
Storage Temperature Range	T _{stg}	–40 to 150	°C

(1) VDRM and VRRM for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



ON Semiconductor

http://onsemi.com

SCRs 0.8 AMPERES RMS 100 thru 600 VOLTS





TO-92 (TO-226AA) CASE 029 STYLE 10

PIN ASSIGNMENT			
1 Cathode			
2	Gate		
3	Anode		

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit	
Thermal Resistance — Junction to Case — Junction to Ambient	R _{θJC} R _{θJA}	75 200	°C/W	
Lead Solder Temperature (<1/16" from case, 10 secs max)	TL	260	°C	

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

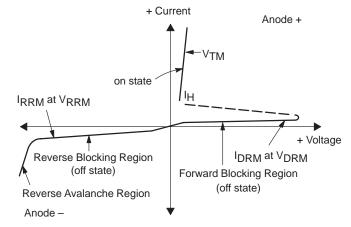
Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Peak Repetitive Forward or Reverse Blocking Current ⁽¹⁾ (V_D = Rated V_{DRM} and V_{RRM} ; R_{GK} = 1 $k\Omega$)	T _C = 25°C T _C = 110°C	I _{DRM} , I _{RRM}	_ _	_	10 100	μА
ON CHARACTERISTICS						
Peak Forward On–State Voltage(*) (I _{TM} = 1.0 Amp Peak @ T _A = 25°C)		V _{TM}		_	1.7	Volts
Gate Trigger Current (Continuous dc) ⁽²⁾ (V _{AK} = 7.0 Vdc, R _L = 100 Ohms)	T _C = 25°C	IGT	_	40	200	μΑ
Holding Current(2) (VAK = 7.0 Vdc, Initiating Current = 20 mA)	$T_C = 25^{\circ}C$ $T_C = -40^{\circ}C$	lн	_	0.5 —	5.0 10	mA
Latch Current $(V_{AK} = 7.0 \text{ V}, \text{ lg} = 200 \mu\text{A})$	$T_C = 25^{\circ}C$ $T_C = -40^{\circ}C$	IL	_	0.6 —	10 15	mA
Gate Trigger Voltage (Continuous dc) ⁽²⁾ (V _{AK} = 7.0 Vdc, R _L = 100 Ohms) T _C = -40°C	T _C = 25°C	VGT	_ _	0.62 —	0.8 1.2	Volts
DYNAMIC CHARACTERISTICS						
Critical Rate of Rise of Off–State Voltage (V_D = Rated V_{DRM} , Exponential Waveform, R_{GK} = 1000 Ohms, T_J = 110°C)		dV/dt	20	35	_	V/μs
Critical Rate of Rise of On–State Current (IpK = 20 A; Pw = 10 µsec; diG/dt = 1 A/µsec, Igt = 20 r	mA)	di/dt	_	_	50	A/μs

^{*}Indicates Pulse Test: Pulse Width ≤ 1.0 ms, Duty Cycle ≤ 1%.

⁽¹⁾ R_{GK} = 1000 Ohms included in measurement. (2) Does not include R_{GK} in measurement.

Voltage Current Characteristic of SCR

Symbol	Parameter
V _{DRM}	Peak Repetitive Off State Forward Voltage
IDRM	Peak Forward Blocking Current
VRRM	Peak Repetitive Off State Reverse Voltage
IRRM	Peak Reverse Blocking Current
VTM	Peak on State Voltage
lH	Holding Current



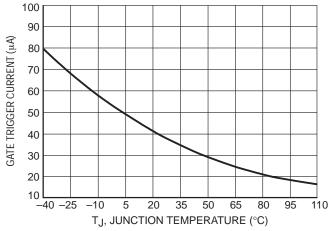


Figure 1. Typical Gate Trigger Current versus Junction Temperature

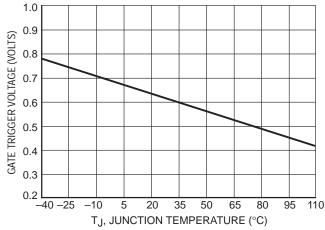
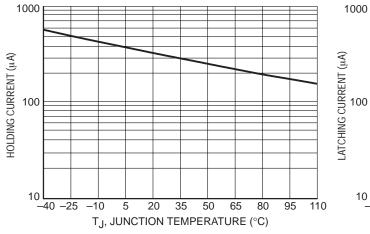


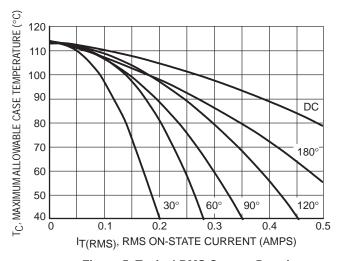
Figure 2. Typical Gate Trigger Voltage versus
Junction Temperature



100 T_J, JUNCTION TEMPERATURE (°C)

Figure 3. Typical Holding Current versus Junction Temperature

Figure 4. Typical Latching Current versus Junction Temperature



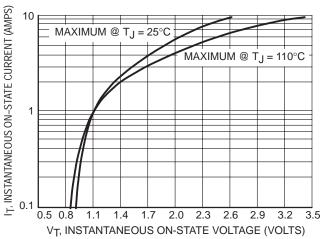


Figure 5. Typical RMS Current Derating

Figure 6. Typical On-State Characteristics

TO-92 EIA RADIAL TAPE IN FAN FOLD BOX OR ON REEL

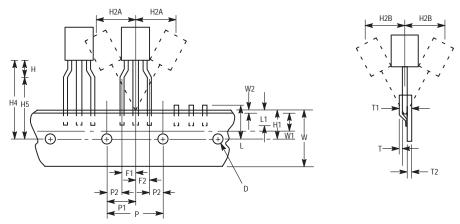


Figure 7. Device Positioning on Tape

			Specification			
		Inc	hes	Millir	neter	
Symbol	Item	Min	Max	Min	Max	
D	Tape Feedhole Diameter	0.1496	0.1653	3.8	4.2	
D2	Component Lead Thickness Dimension	0.015	0.020	0.38	0.51	
F1, F2	Component Lead Pitch	0.0945	0.110	2.4	2.8	
Н	Bottom of Component to Seating Plane	.059	.156	1.5	4.0	
H1	Feedhole Location	0.3346	0.3741	8.5	9.5	
H2A	Deflection Left or Right	0	0.039	0	1.0	
H2B	Deflection Front or Rear	0	0.051	0	1.0	
H4	Feedhole to Bottom of Component	0.7086	0.768	18	19.5	
H5	Feedhole to Seating Plane	0.610	0.649	15.5	16.5	
L	Defective Unit Clipped Dimension	0.3346	0.433	8.5	11	
L1	Lead Wire Enclosure	0.09842	_	2.5	_	
Р	Feedhole Pitch	0.4921	0.5079	12.5	12.9	
P1	Feedhole Center to Center Lead	0.2342	0.2658	5.95	6.75	
P2	First Lead Spacing Dimension	0.1397	0.1556	3.55	3.95	
Т	Adhesive Tape Thickness	0.06	0.08	0.15	0.20	
T1	Overall Taped Package Thickness	_	0.0567	_	1.44	
T2	Carrier Strip Thickness	0.014	0.027	0.35	0.65	
W	Carrier Strip Width	0.6889	0.7481	17.5	19	
W1	Adhesive Tape Width	0.2165	0.2841	5.5	6.3	
W2	Adhesive Tape Position	.0059	0.01968	.15	0.5	

NOTES:

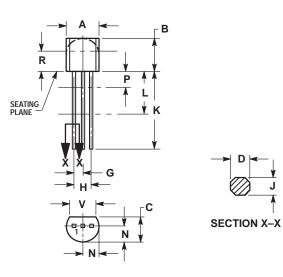
- 1. Maximum alignment deviation between leads not to be greater than 0.2 mm.
- 2. Defective components shall be clipped from the carrier tape such that the remaining protrusion (L) does not exceed a maximum of 11 mm.
- 3. Component lead to tape adhesion must meet the pull test requirements.
- 4. Maximum non-cumulative variation between tape feed holes shall not exceed 1 mm in 20 pitches.
- 5. Holddown tape not to extend beyond the edge(s) of carrier tape and there shall be no exposure of adhesive.
- 6. No more than 1 consecutive missing component is permitted.
- 7. A tape trailer and leader, having at least three feed holes is required before the first and after the last component.
- 8. Splices will not interfere with the sprocket feed holes.

ORDERING & SHIPPING INFORMATION: MCR100 Series packaging options, Device Suffix

U.S.	Europe Equivalent	Shipping	Description of TO92 Tape Orientation
MCR100-3,4,6,8 MCR100-6RLRA MCR100-6RLRM	MCR100-3RL,6RL,8RL MCR100-6ZL1	Bulk in Box (5K/Box) Radial Tape and Reel (2K/Reel) Radial Tape and Fan Fold Box (2K/Box)	N/A, Bulk Round side of TO92 and adhesive tape visible Flat side of TO92 and adhesive tape visible

PACKAGE DIMENSIONS

TO-92 (TO-226AA) CASE 029-11 **ISSUE AJ**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
V	0.135		3 43	

STYLE 10: PIN 1. CATHODE 2. GATE 3. ANODE

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